

Product Summary

BV_{DSS}	R_{DS(ON)}	I_D T_C = +25°C
40V	4.0mΩ @ V _{GS} = 10V	150A

Description and Applications

This new generation enhancement mode MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

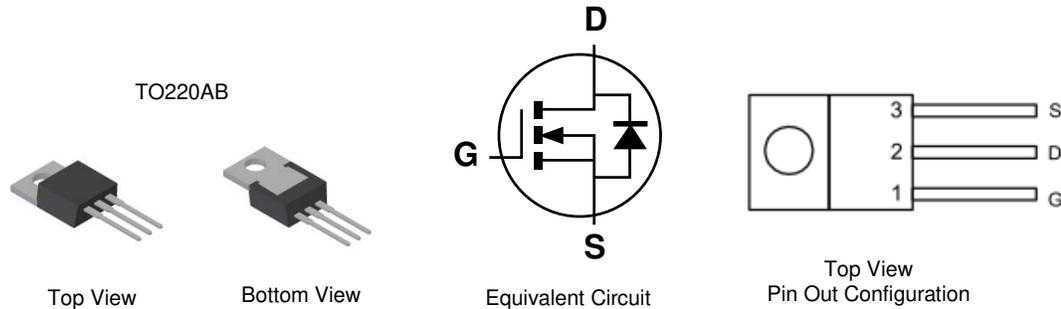
- Motor controls
- Backlighting
- DC-DC converters
- Power-management functions

Features and Benefits

- Low Input Capacitance
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.**
<https://www.diodes.com/quality/product-definitions/>
- **An automotive-compliant part is available under separate datasheet ([DMNH4005SCTQ](#))**

Mechanical Data

- Package: TO220AB
- Package Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓔ³
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)

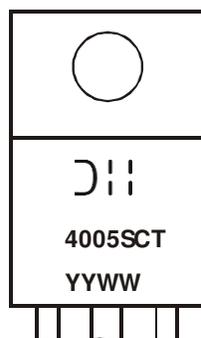


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMNH4005SCT	TO220AB	50	Tube

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



D||| = Manufacturer's Marking
 4005SCT = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 23 = 2023)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	40	V
Gate-Source Voltage			V _{GSS}	20	V
Continuous Drain Current V _{GS} = 10V	Steady State	T _C = +25°C	I _D	150	A
		T _C = +100°C		100	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	600	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	80	A
Avalanche Current (Note 6) L=1mH			I _{AS}	30	A
Avalanche Energy (Note 6) L=1mH			E _{AS}	500	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation	T _C = +25°C	P _D	165	W
	T _C = +70°C		100	
Thermal Resistance, Junction to Case		R _{θJC}	0.9	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 32V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.4	4.0	mΩ	V _{GS} = 10V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	2846	—	pF	V _{DS} = 20V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	742	—		
Reverse Transfer Capacitance	C _{rss}	—	242	—		
Gate Resistance	R _G	—	1.9	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	48	—	nC	V _{DD} = 20V, I _D = 20A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	23	—		
Gate-Source Charge	Q _{gs}	—	9.5	—		
Gate-Drain Charge	Q _{gd}	—	11.5	—		
Turn-On Delay Time	t _{D(ON)}	—	6.6	—	ns	V _{DD} = 20V, V _{GS} = 10V, R _G = 1Ω, I _D = 20A
Turn-On Rise Time	t _R	—	12.1	—		
Turn-Off Delay Time	t _{D(OFF)}	—	18.3	—		
Turn-Off Fall Time	t _F	—	4.9	—		
Reverse Recovery Time	t _{RR}	—	29	—	ns	I _F = 15A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	24	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

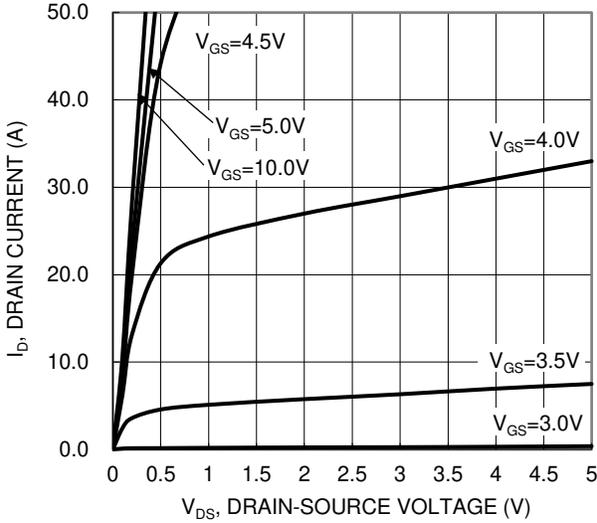


Figure 1. Typical Output Characteristic

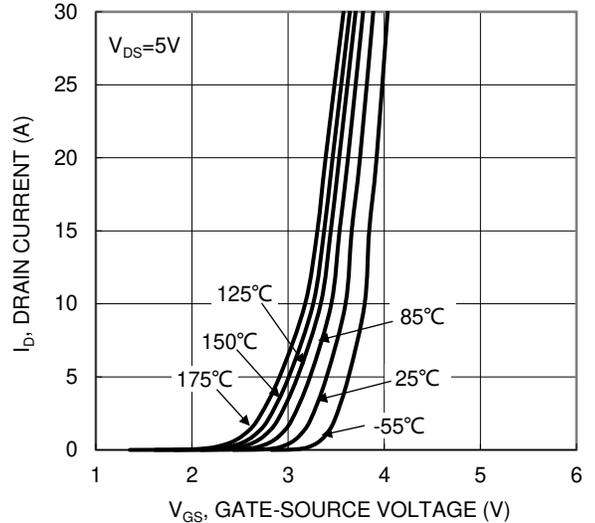


Figure 2. Typical Transfer Characteristic

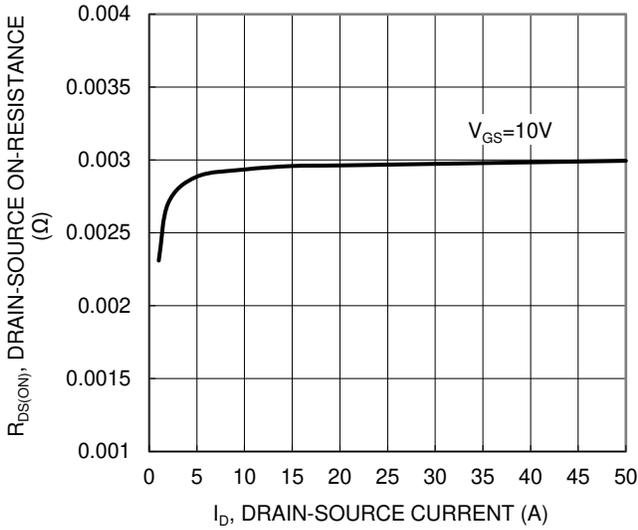


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

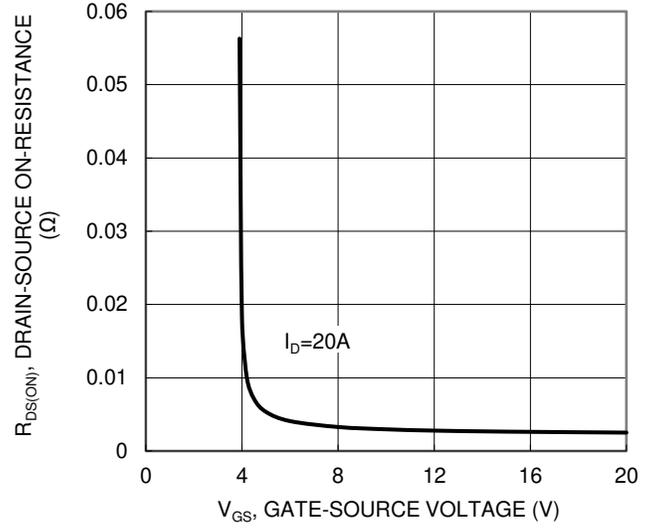


Figure 4. Typical Transfer Characteristic

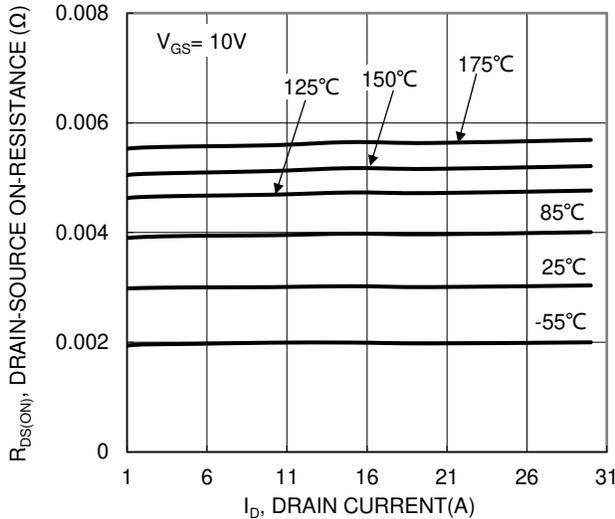


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

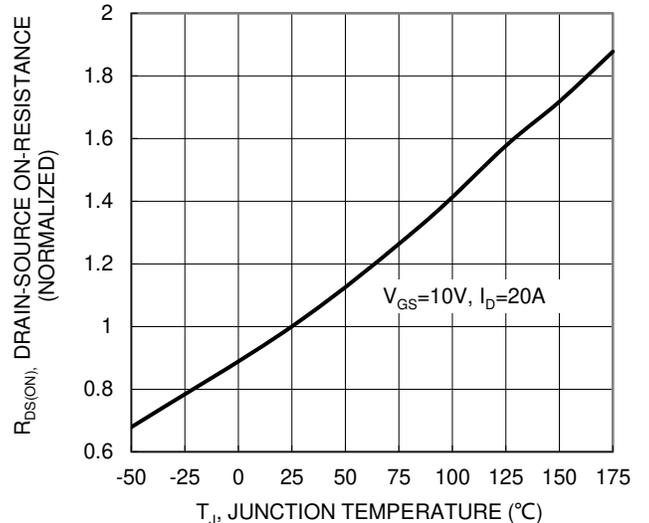


Figure 6. On-Resistance Variation with Junction Temperature

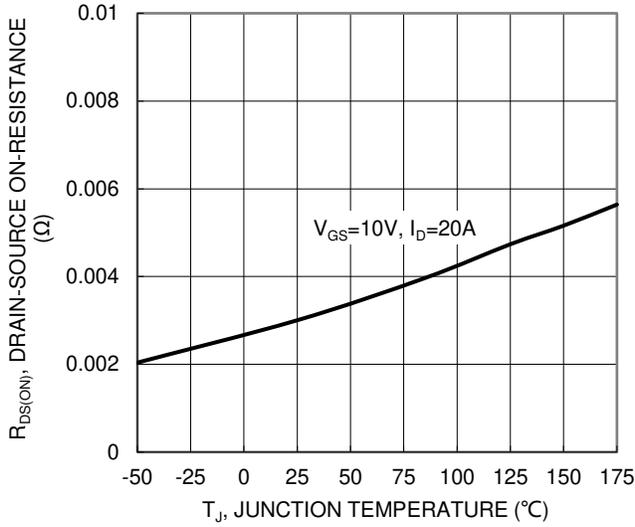


Figure 7. On-Resistance Variation with Junction Temperature

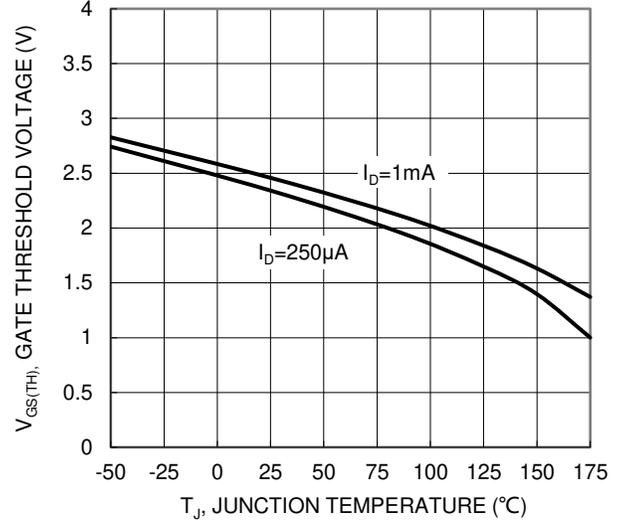


Figure 8. Gate Threshold Variation vs. Junction Temperature

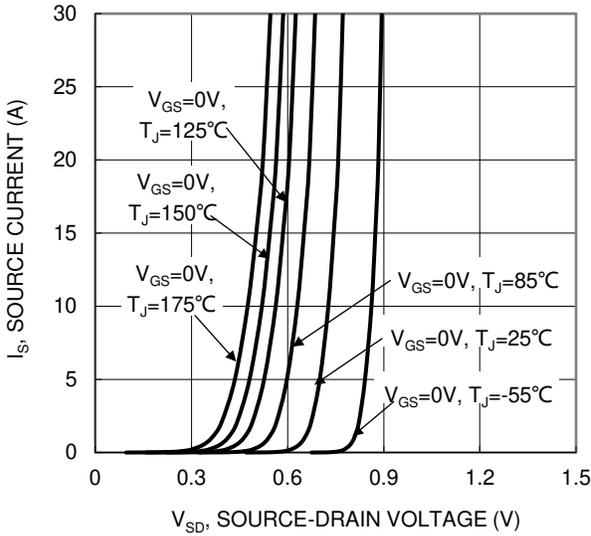


Figure 9. Diode Forward Voltage vs. Current

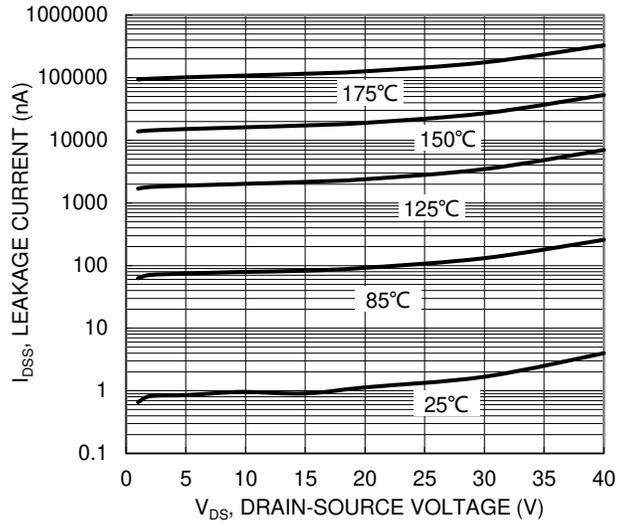


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

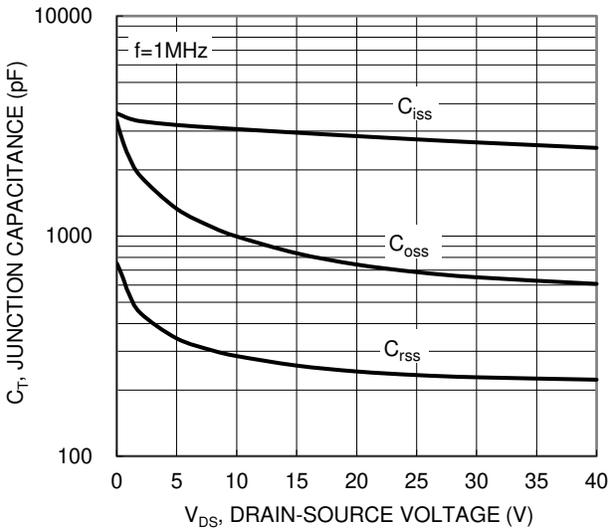


Figure 11. Typical Junction Capacitance

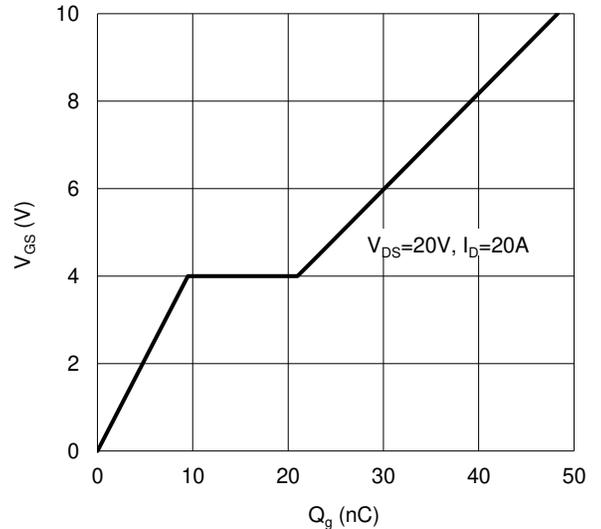


Figure 12. Gate Charge

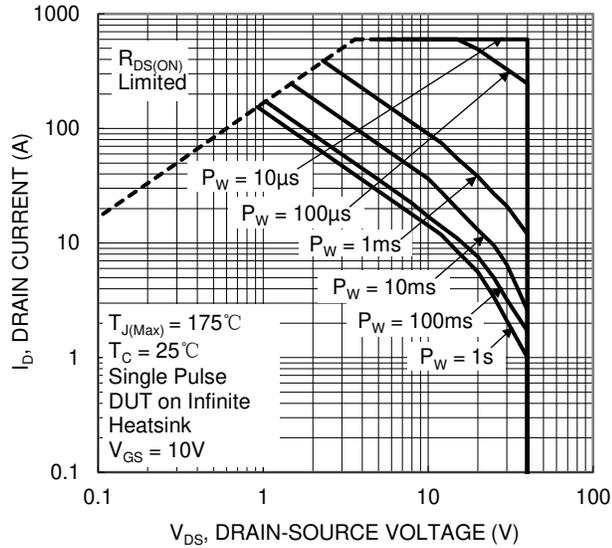


Figure 13. SOA, Safe Operation Area

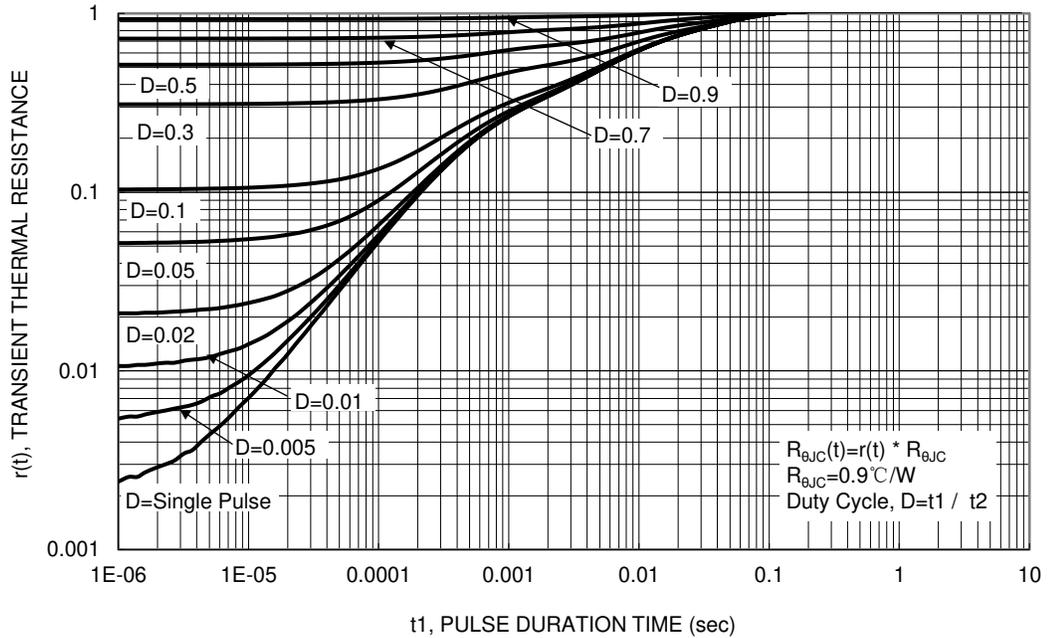
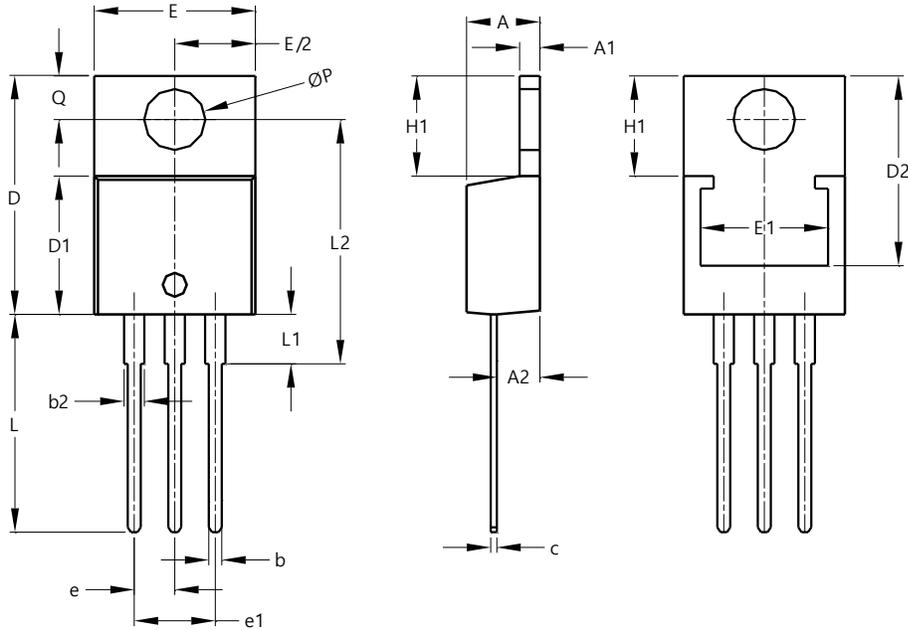


Figure 14. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO220AB



TO220AB			
Dim	Min	Max	Typ
A	3.56	4.82	-
A1	0.51	1.39	-
A2	2.04	2.92	-
b	0.39	1.01	0.81
b2	1.15	1.77	1.24
c	0.356	0.61	-
D	14.22	16.51	-
D1	8.39	9.01	-
D2	11.45	12.87	-
e	-	-	2.54
e1	-	-	5.08
E	9.66	10.66	-
E1	6.86	8.89	-
H1	5.85	6.85	-
L	12.70	14.73	-
L1	-	4.42	-
L2	15.80	17.51	16.00
P	3.54	4.08	-
Q	2.54	3.42	-
All Dimensions in mm			

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